

MBR4015CTLG

Switch-mode Power Rectifier

Features and Benefits

- Low Forward Voltage
- Low Power Loss/High Efficiency
- High Surge Capacity
- 150°C Operating Junction Temperature
- 40 A Total (20 A Per Diode Leg)
- This Device is Pb-Free and is RoHS Compliant*

Applications

- Power Supply – Output Rectification
- Power Management
- Instrumentation

Mechanical Characteristics

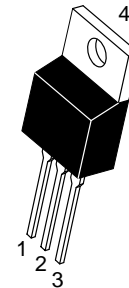
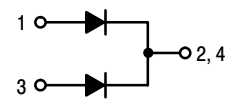
- Case: Epoxy, Molded
- Epoxy Meets UL 94, V-0 @ 0.125 in
- Weight: 1.9 Grams (Approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperatures for Soldering Purposes: 260°C Max. for 10 Seconds
- ESD Rating: Human Body Model 3B
Machine Model C



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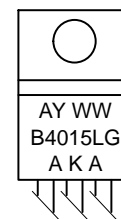
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SCHOTTKY BARRIER RECTIFIER 40 AMPERES, 15 VOLTS



TO-220
STYLE 6
CASE 221A

MARKING DIAGRAM



A = Assembly Location
Y = Year
WW = Work Week
B4015L = Device Code
G = Pb-Free Package
AKA = Polarity Designator

ORDERING INFORMATION

Device	Package	Shipping
MBR4015CTLG	TO-220 (Pb-Free)	50 Units/Rail

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MBR4015CTLG

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	15	V
Average Rectified Forward Current ($T_C = 140^\circ\text{C}$ per Diode) ($T_C = 140^\circ\text{C}$ per Device)	$I_{F(AV)}$	20 40	A
Peak Repetitive Forward Current, per Diode (Square Wave, 20 kHz, $T_C = 135^\circ\text{C}$)	I_{FRM}	40	A
Non-Repetitive Peak Surge Current (Surge Applied at Rated Load Conditions, Halfwave, Single Phase, 60 Hz)	I_{FSM}	150	A
Peak Repetitive Reverse Surge Current (2.0 μs , 1.0 kHz)	I_{RRM}	1.0	A
Storage Temperature Range	T_{stg}	-65 to +175	$^\circ\text{C}$
Operating Junction Temperature (Note 1)	T_J	-65 to +150	$^\circ\text{C}$
Voltage Rate of Change (Rated V_R)	dv/dt	1,000	V/ μs

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. The heat generated must be less than the thermal conductivity from Junction-to-Ambient: $dP_D/dT_J < 1/R_{\theta JA}$.

THERMAL CHARACTERISTICS (Per Diode)

Characteristic	Conditions	Symbol	Max	Unit
Maximum Thermal Resistance, Junction-to-Case	Min. Pad	$R_{\theta JC}$	1.3	$^\circ\text{C}/\text{W}$
Maximum Thermal Resistance, Junction-to-Ambient	Min. Pad	$R_{\theta JA}$	70	

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Min	Typical	Max	Unit
Instantaneous Forward Voltage (Note 2) ($i_F = 20\text{ A}$, $T_J = 125^\circ\text{C}$) ($i_F = 40\text{ A}$, $T_J = 125^\circ\text{C}$) ($i_F = 20\text{ A}$, $T_J = 25^\circ\text{C}$) ($i_F = 40\text{ A}$, $T_J = 25^\circ\text{C}$)	V_F	-	0.31 0.45 0.41 0.51	0.34 0.50 0.43 0.54	V
Instantaneous Reverse Current (Note 2) (Rated dc Voltage, $T_J = 125^\circ\text{C}$) (Rated dc Voltage, $T_J = 25^\circ\text{C}$)	i_R	-	300 0.8	600 10	mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Test: Pulse Width = 300 μs , Duty Cycle $\leq 2.0\%$.

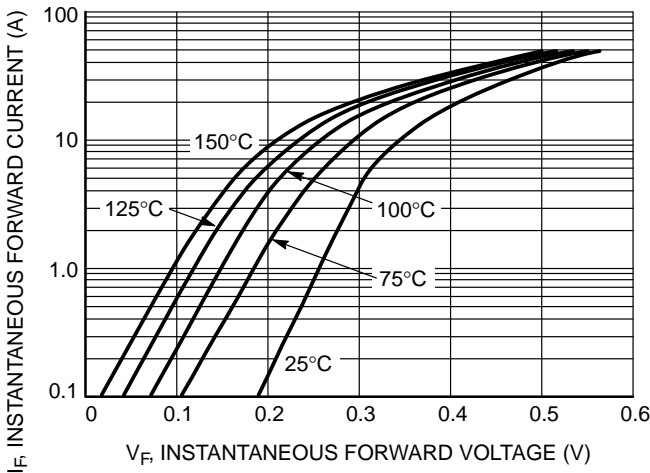


Figure 1. Typical Forward Voltage

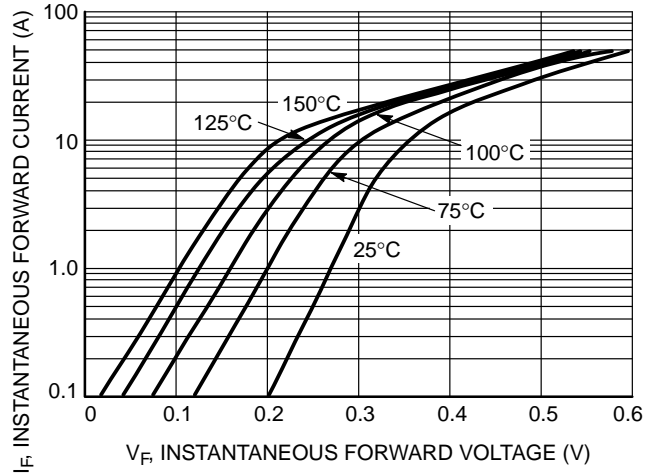


Figure 2. Maximum Forward Voltage

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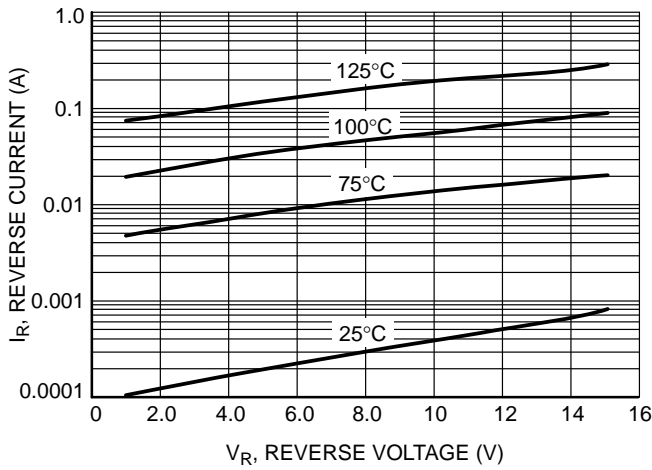


Figure 3. Typical Reverse Current

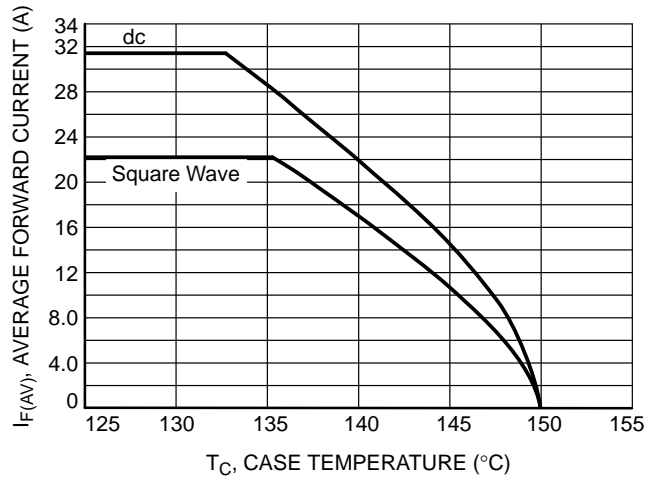


Figure 4. Current Derating, Case, Per Leg

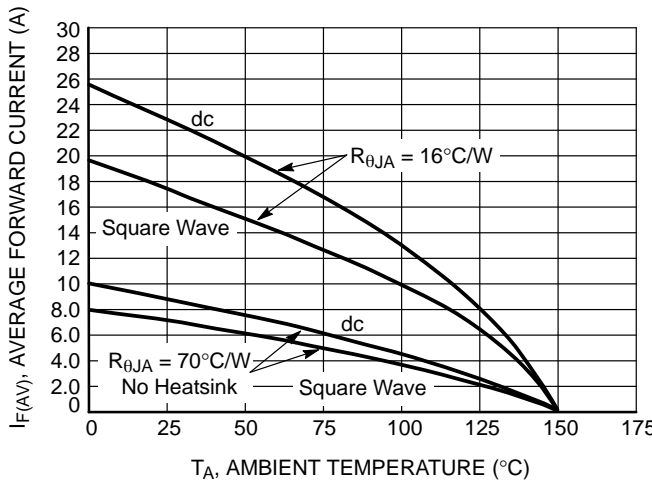


Figure 5. Current Derating, Ambient, Per Leg

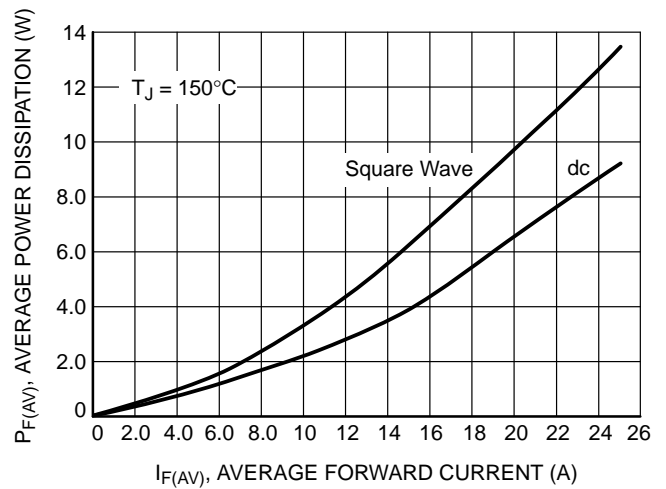


Figure 6. Forward Power Dissipation

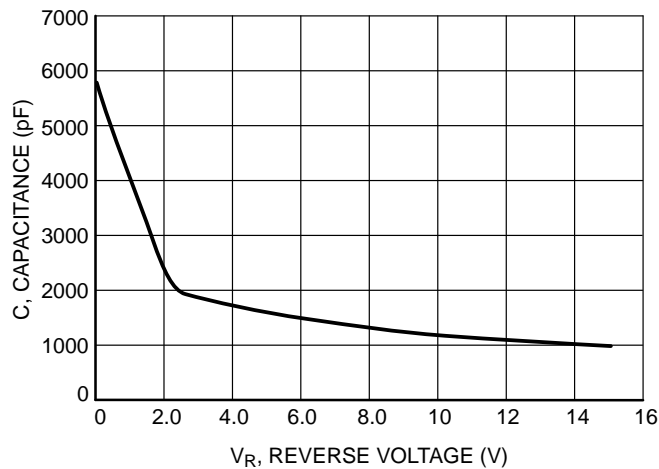
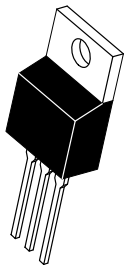


Figure 7. Typical Capacitance

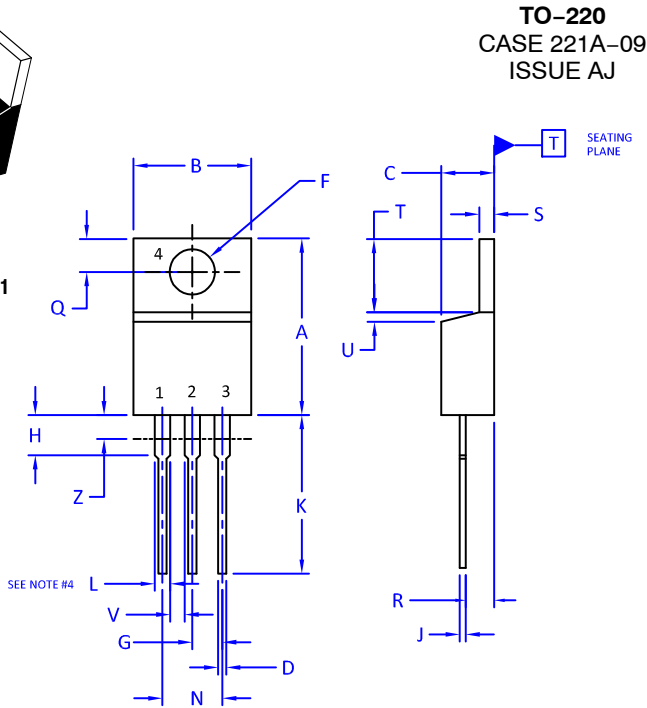
MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

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SCALE 1:1



TO-220 CASE 221A-09 ISSUE AJ

DATE 05 NOV 2019

NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 2009.
2. CONTROLLING DIMENSION: INCHES
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.
4. MAX WIDTH FOR F102 DEVICE = 1.35MM

DIM	INCHES		MILLIMETERS	
	MIN.	MAX.	MIN.	MAX.
A	0.570	0.620	14.48	15.75
B	0.380	0.415	9.66	10.53
C	0.160	0.190	4.07	4.83
D	0.025	0.038	0.64	0.96
F	0.142	0.161	3.60	4.09
G	0.095	0.105	2.42	2.66
H	0.110	0.161	2.80	4.10
J	0.014	0.024	0.36	0.61
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.41
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

STYLE 1:

- PIN 1. BASE
- 2. COLLECTOR
- 3. EMITTER
- 4. COLLECTOR

STYLE 2:

- PIN 1. BASE
- 2. EMITTER
- 3. COLLECTOR
- 4. EMITTER

STYLE 3:

- PIN 1. CATHODE
- 2. ANODE
- 3. GATE
- 4. ANODE

STYLE 4:

- PIN 1. MAIN TERMINAL 1
- 2. MAIN TERMINAL 2
- 3. GATE
- 4. MAIN TERMINAL 2

STYLE 5:

- PIN 1. GATE
- 2. DRAIN
- 3. SOURCE
- 4. DRAIN

STYLE 6:

- PIN 1. ANODE
- 2. CATHODE
- 3. ANODE
- 4. CATHODE

STYLE 7:

- PIN 1. CATHODE
- 2. ANODE
- 3. CATHODE
- 4. ANODE

STYLE 8:

- PIN 1. CATHODE
- 2. ANODE
- 3. EXTERNAL TRIP/DELAY
- 4. ANODE

STYLE 9:

- PIN 1. GATE
- 2. COLLECTOR
- 3. EMITTER
- 4. COLLECTOR

STYLE 10:

- PIN 1. GATE
- 2. SOURCE
- 3. DRAIN
- 4. SOURCE

STYLE 11:

- PIN 1. DRAIN
- 2. SOURCE
- 3. GATE
- 4. SOURCE

STYLE 12:

- PIN 1. MAIN TERMINAL 1
- 2. MAIN TERMINAL 2
- 3. GATE
- 4. NOT CONNECTED

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